

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

OptiMOS™

OptiMOS™ Power-MOSFET, 40 V
BSC010N04LS

Data Sheet

Rev. 2.2
Final

Power Management & Multimarket

1 Description

Features

- Optimized for synchronous rectification
- Very low on-resistance $R_{DS(on)}$
- 100% avalanche tested
- Superior thermal resistance
- N-channel, logic level
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Higher solder joint reliability due to enlarged source interconnection

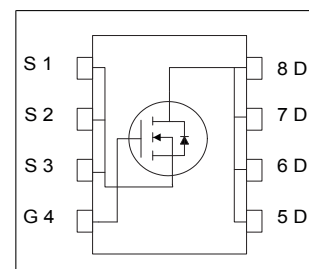
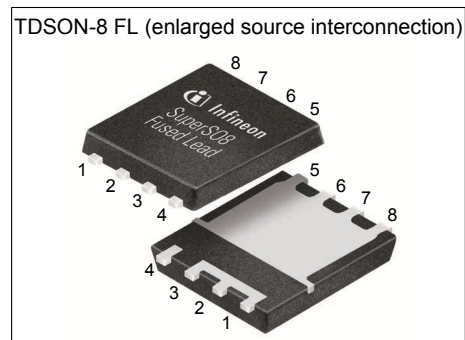


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	40	V
$R_{DS(on),max}$	1.0	$m\Omega$
I_D	100	A
Q_{oss}	84	nC
$Q_g(0V..10V)$	95	nC

Type / Ordering Code	Package	Marking	Related Links
BSC010N04LS	TDSO8-8 FL	010N04LS	-

¹⁾ J-STD20 and JESD22

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2 Maximum ratings

at $T_j = 25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	100	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=4.5\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=4.5\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=50\text{ K/W}^1)$
		-	-	100		
		-	-	100		
		-	-	100		
		-	-	38		
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	400	A	$T_C=25\text{ °C}$
Avalanche current, single pulse ³⁾	I_{AS}	-	-	50	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	E_{AS}	-	-	330	mJ	$I_D=50\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	139	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=50\text{ K/W}^1)$
		-	-	2.5		
Operating and storage temperature	T_j, T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

3 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	0.5	0.9	K/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	-	20	K/W	-
Device on PCB, 6 cm ² cooling area ¹⁾	R_{thJA}	-	-	50	K/W	-

¹⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

²⁾ See figure 3 for more detailed information

³⁾ See figure 13 for more detailed information

4 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	40	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	1.2	-	2	V	$V_{DS}=V_{GS}$, $I_D=250\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=40\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ }^\circ\text{C}$ $V_{DS}=40\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ }^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.0 0.85	1.3 1.0	m Ω	$V_{GS}=4.5\text{ V}$, $I_D=50\text{ A}$ $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$
Gate resistance ¹⁾	R_G	-	0.8	1.6	Ω	-
Transconductance	g_{fs}	140	270	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=50\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance ¹⁾	C_{iss}	-	6800	9520	pF	$V_{GS}=0\text{ V}$, $V_{DS}=20\text{ V}$, $f=1\text{ MHz}$
Output capacitance ¹⁾	C_{oss}	-	1900	2660	pF	$V_{GS}=0\text{ V}$, $V_{DS}=20\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ¹⁾	C_{rss}	-	160	320	pF	$V_{GS}=0\text{ V}$, $V_{DS}=20\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	10	-	ns	$V_{DD}=20\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_{G,ext,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	12	-	ns	$V_{DD}=20\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_{G,ext,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	46	-	ns	$V_{DD}=20\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_{G,ext,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	9	-	ns	$V_{DD}=20\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_{G,ext,ext}=1.6\text{ }\Omega$

¹⁾ Defined by design. Not subject to production test

Table 6 Gate charge characteristics¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	16	-	nC	$V_{DD}=20\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	11	-	nC	$V_{DD}=20\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge ²⁾	Q_{gd}	-	15	21	nC	$V_{DD}=20\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	21	-	nC	$V_{DD}=20\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ²⁾	Q_g	-	95	133	nC	$V_{DD}=20\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	2.4	-	V	$V_{DD}=20\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ²⁾	Q_g	-	49	69	nC	$V_{DD}=20\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	84	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ²⁾	Q_{oss}	-	84	118	nC	$V_{DD}=20\text{ V}$, $V_{GS}=0\text{ V}$

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	100	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	400	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.81	1	V	$V_{GS}=0\text{ V}$, $I_F=50\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery time ²⁾	t_{rr}	-	36	72	ns	$V_R=20\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=400\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	50	-	nC	$V_R=20\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=400\text{ A}/\mu\text{s}$

¹⁾ See "Gate charge waveforms" for parameter definition

²⁾ Defined by design. Not subject to production test

5 Electrical characteristics diagrams

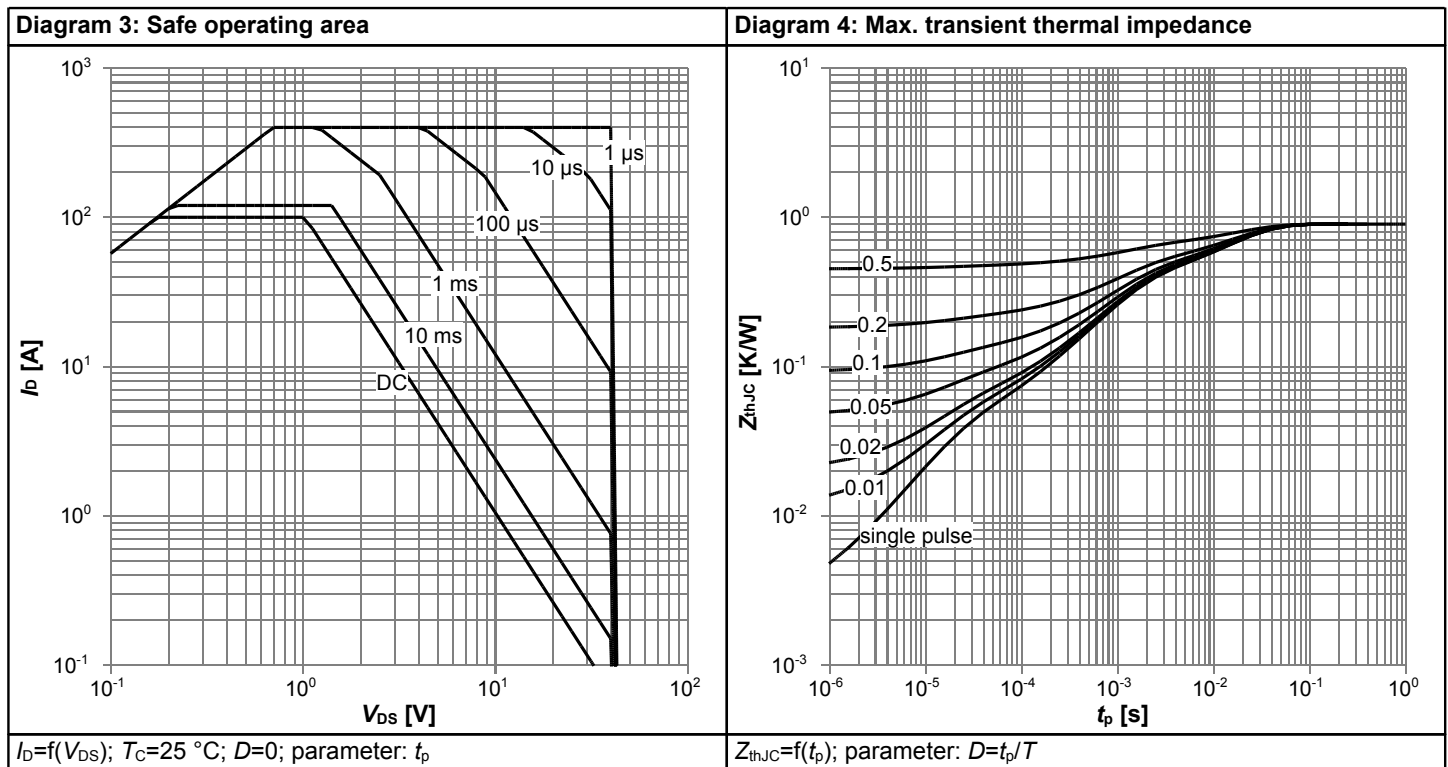
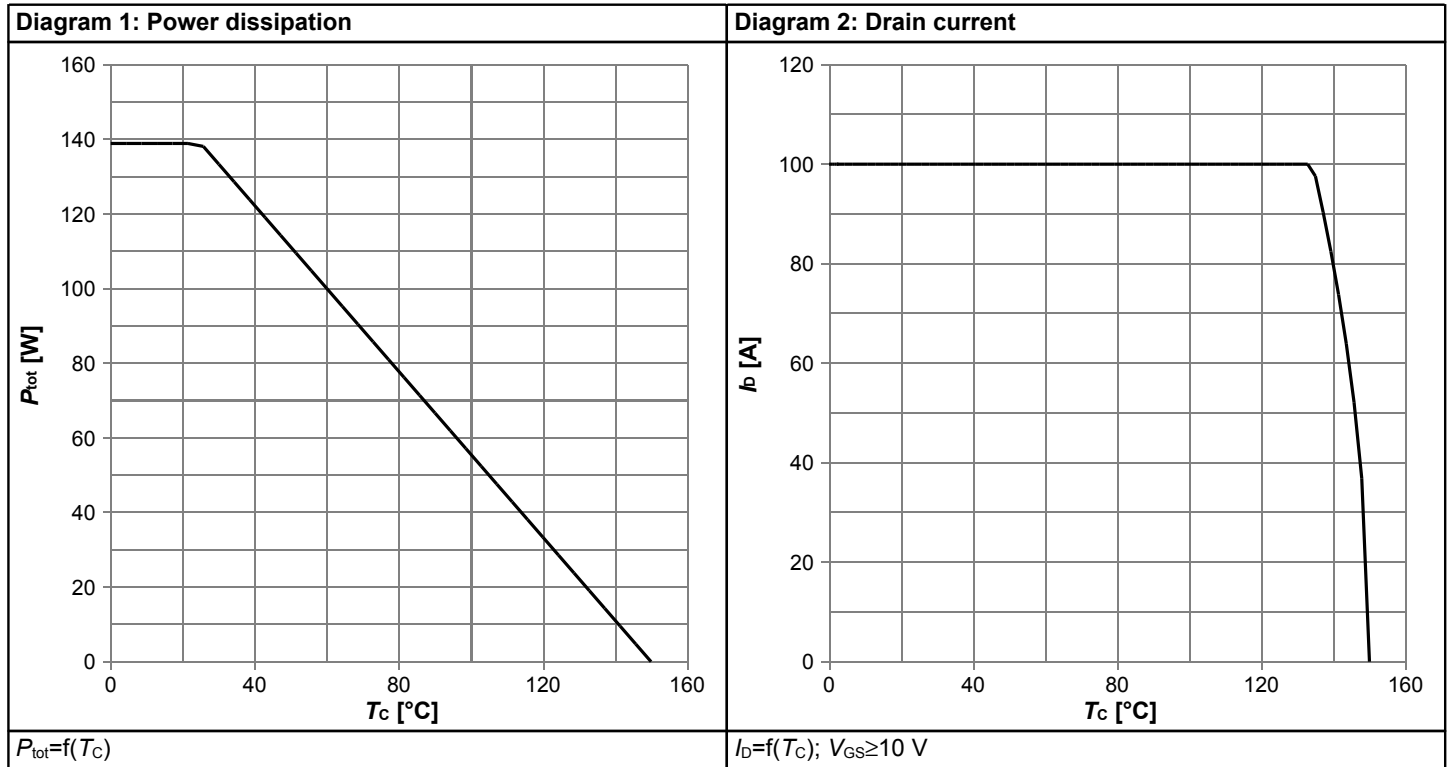
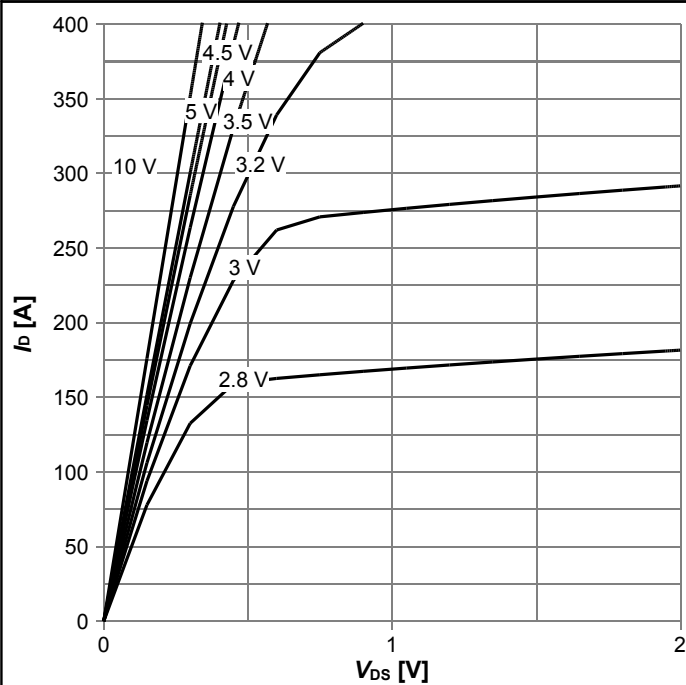
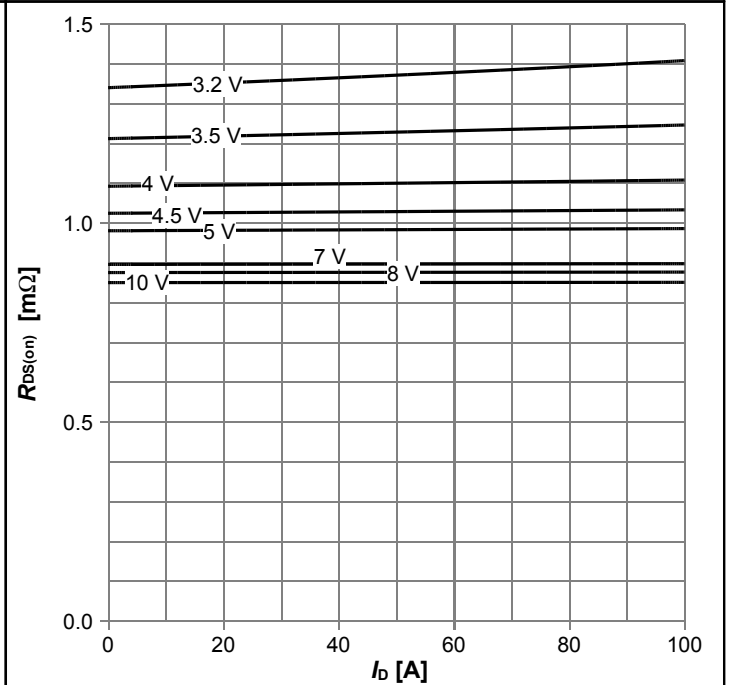


Diagram 5: Typ. output characteristics



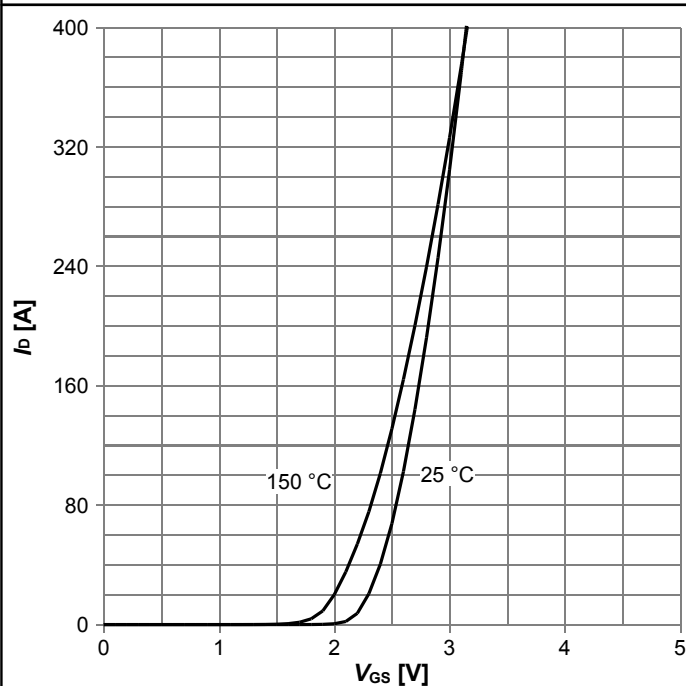
$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C};$ parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



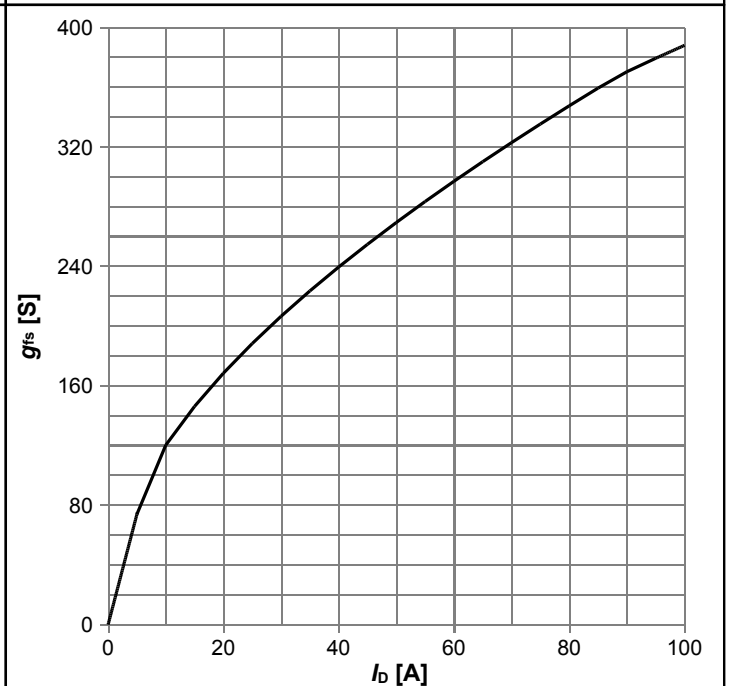
$R_{DS(on)}=f(I_D); T_j=25\text{ }^\circ\text{C};$ parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



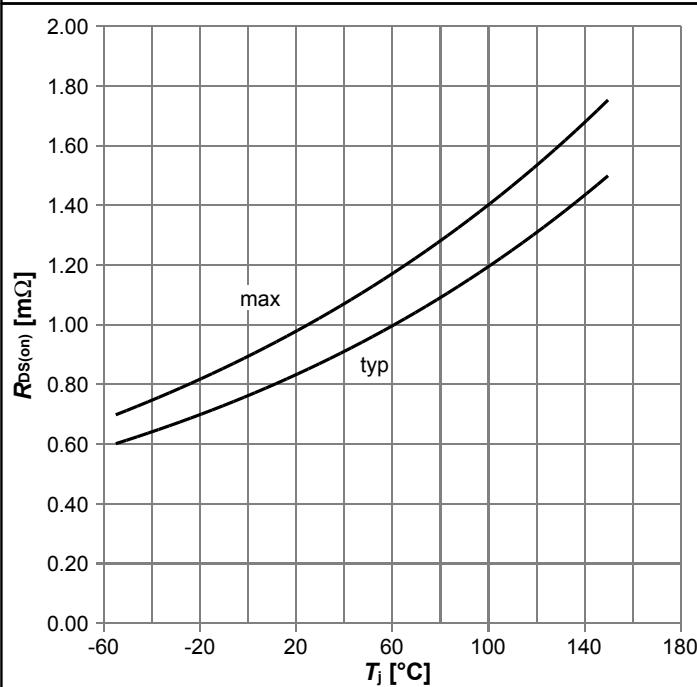
$I_D=f(V_{GS}); |V_{DS}|>2|I_D|R_{DS(on)max};$ parameter: T_j

Diagram 8: Typ. forward transconductance



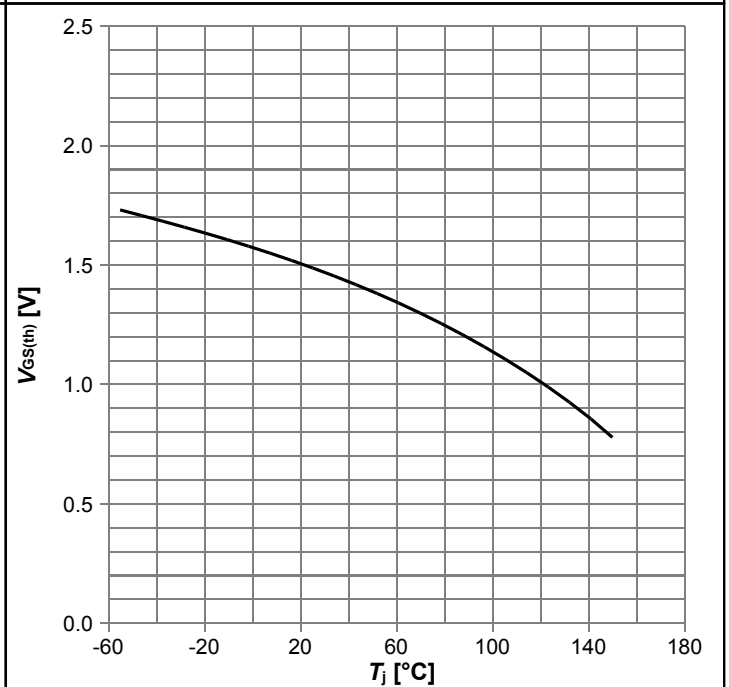
$g_{fs}=f(I_D); T_j=25\text{ }^\circ\text{C}$

Diagram 9: Drain-source on-state resistance



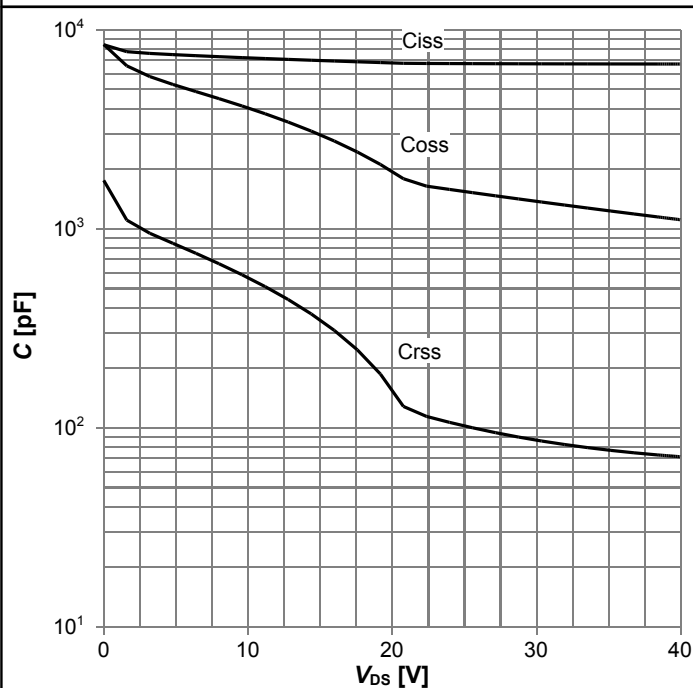
$R_{DS(on)}=f(T_j)$; $I_D=50\text{ A}$; $V_{GS}=10\text{ V}$

Diagram 10: Typ. gate threshold voltage



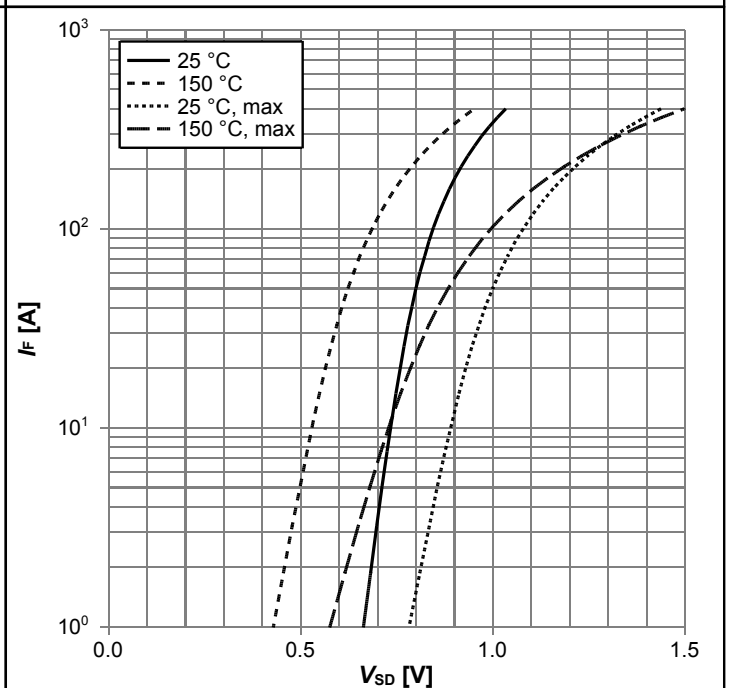
$V_{GS(th)}=f(T_j)$; $V_{GS}=V_{DS}$; $I_D=250\text{ }\mu\text{A}$

Diagram 11: Typ. capacitances



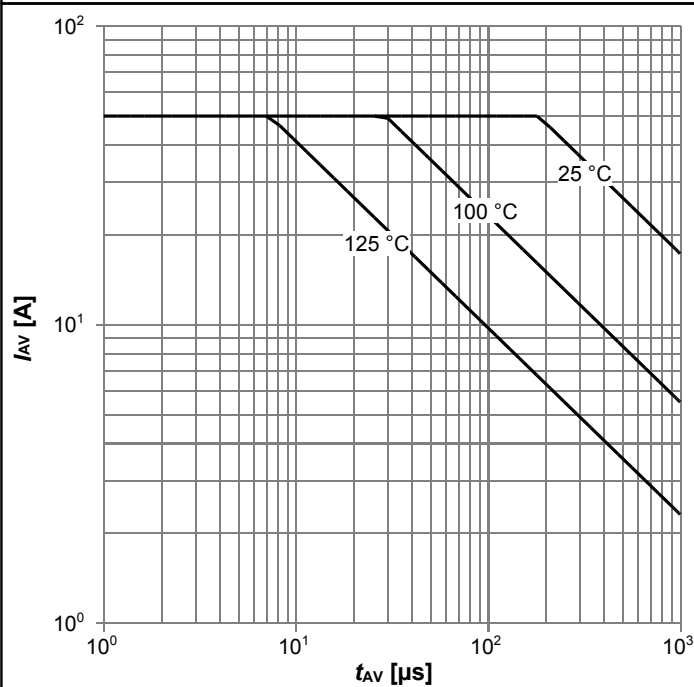
$C=f(V_{DS})$; $V_{GS}=0\text{ V}$; $f=1\text{ MHz}$

Diagram 12: Forward characteristics of reverse diode



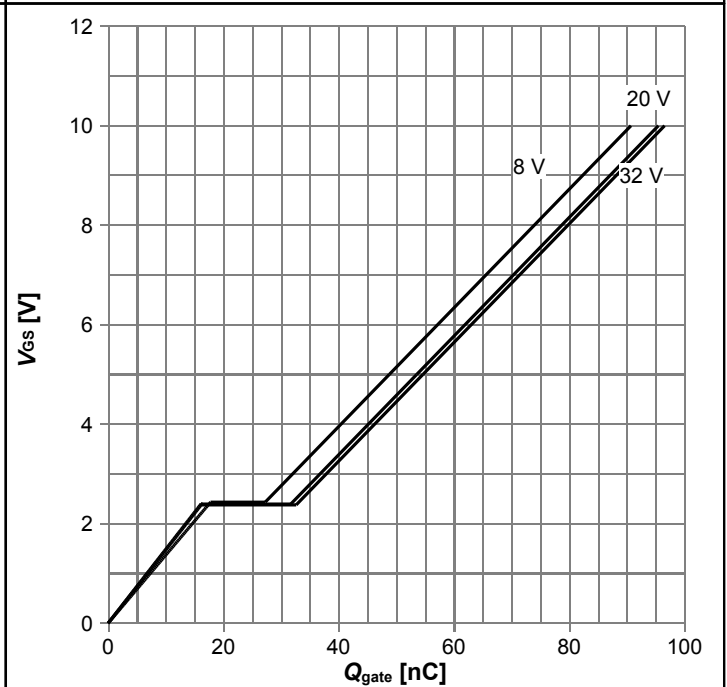
$I_F=f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



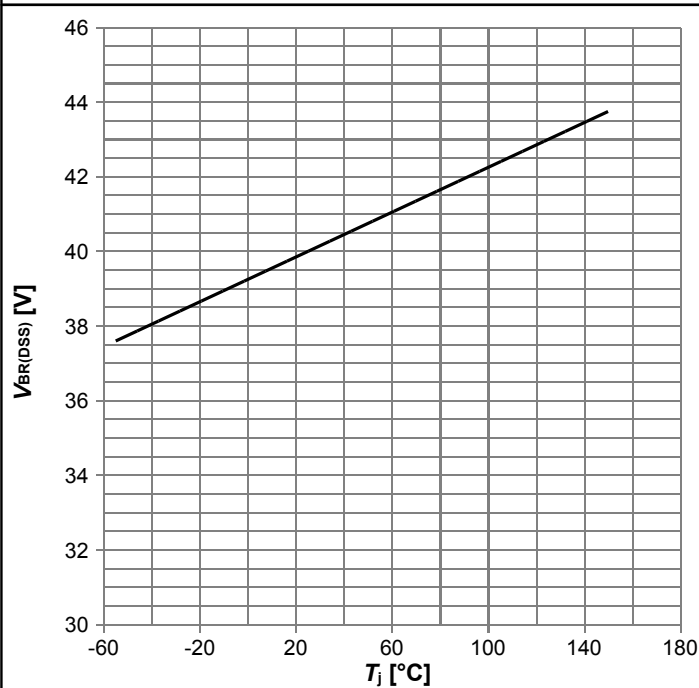
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



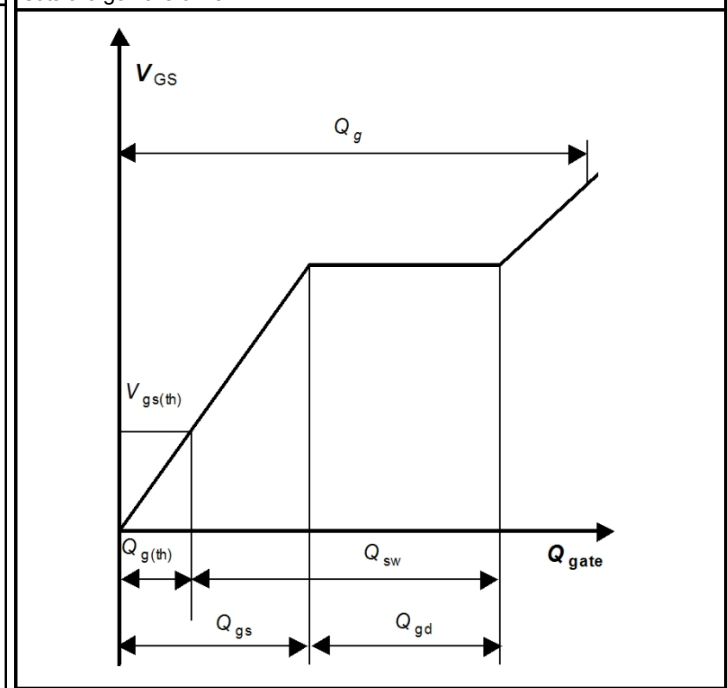
$V_{GS}=f(Q_{gate}); I_D=50$ A pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

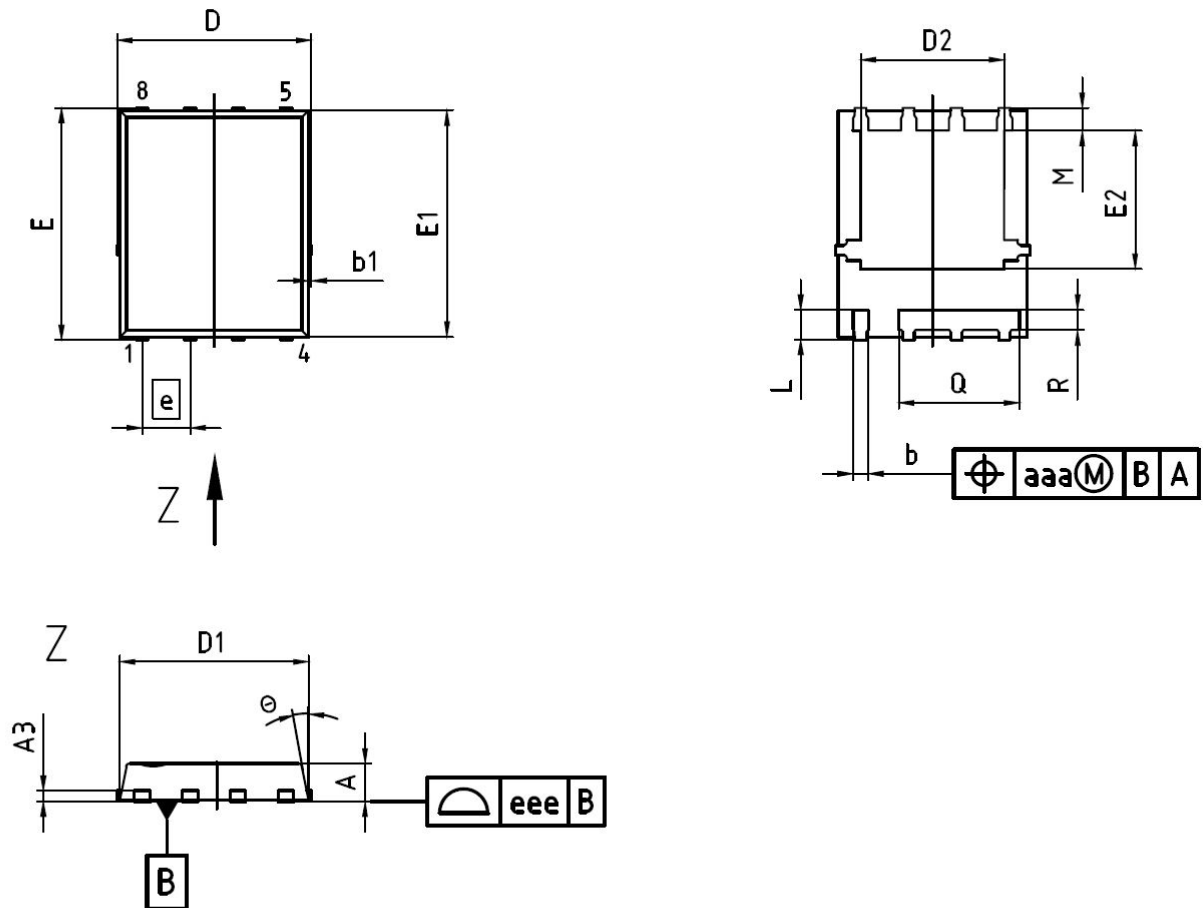


$V_{BR(DSS)}=f(T_j); I_D=1$ mA

Gate charge waveforms



6 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
A3	0.25 (REF)		0.011 (REF)	
b	0.34	0.54	0.013	0.021
b1	0.02	0.22	0.001	0.009
D	5.15 (BSC)		0.203 (BSC)	
D1	5.00 (BSC)		0.197 (BSC)	
D2	3.70	4.40	0.146	0.173
E	6.15 (BSC)		0.242 (BSC)	
E1	6.00 (BSC)		0.236 (BSC)	
E2	3.40	3.80	0.134	0.150
e	1.27 (BSC)		0.050 (BSC)	
N	8		8	
L	0.74	0.84	0.029	0.033
M	0.45	0.66	0.018	0.026
θ	8.5°	12°	8.5°	12°
Q	3.15	3.25	0.124	0.128
R	0.48	0.58	0.019	0.023
aaa	0.25		0.010	
eee	0.08		0.003	

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SCALE

EUROPEAN PROJECTION

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REVISION
01

Figure 1 Outline TDSON-8 FL, dimensions in mm/inches

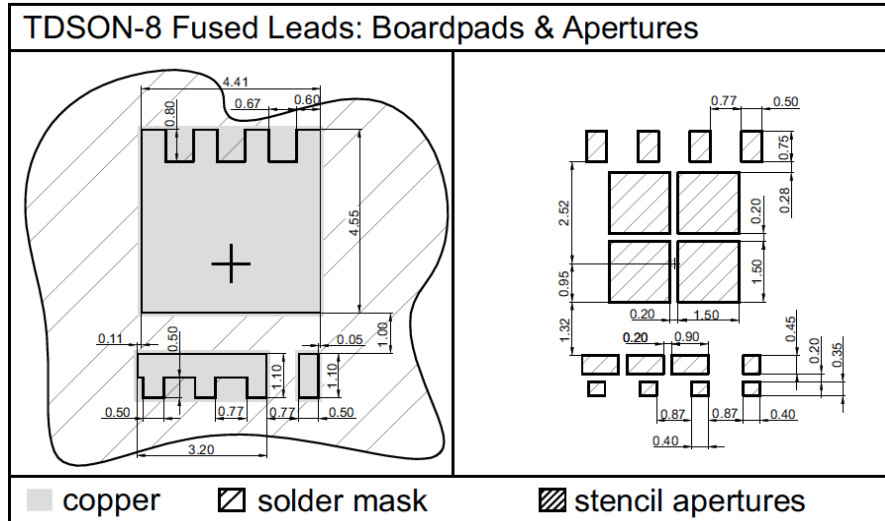


Figure 2 Outline Footprint TDSON-8 FL

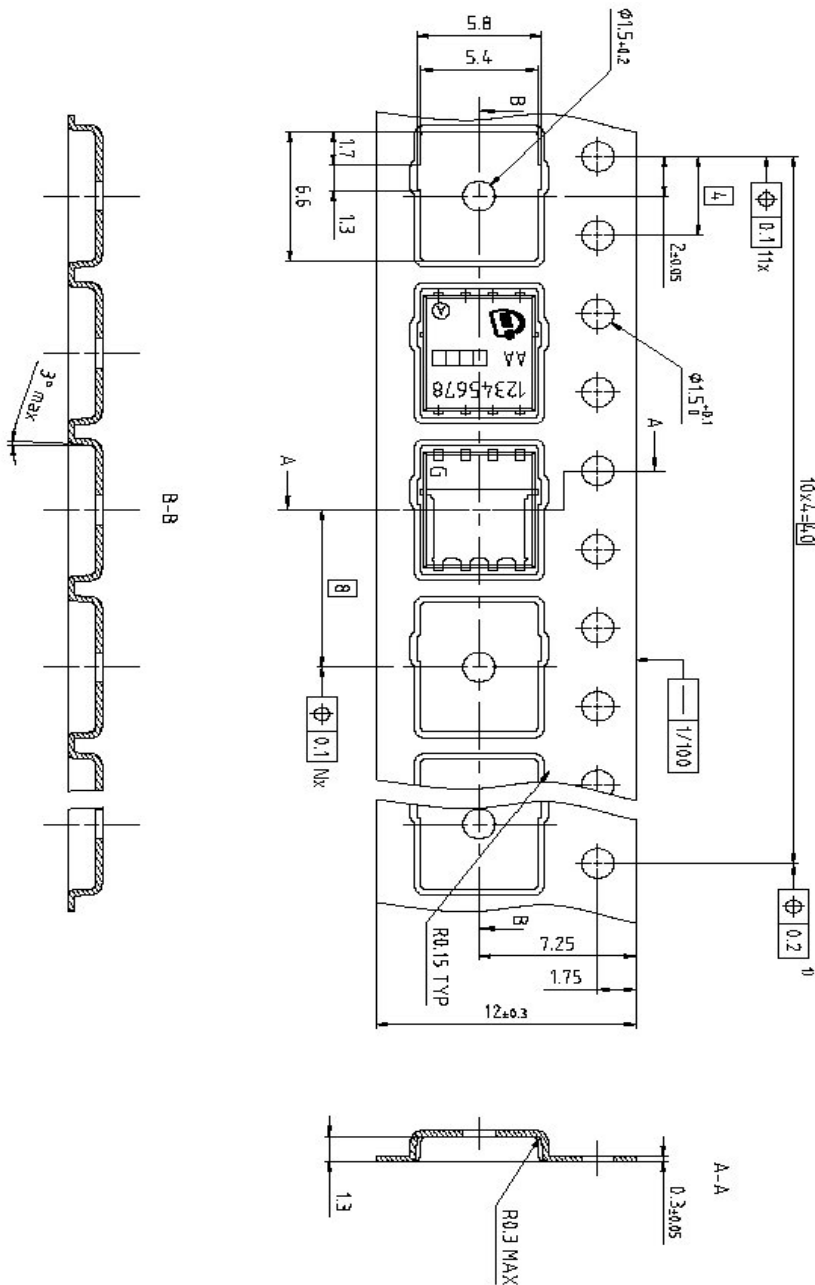


Figure 3 Outline TDSON-8 FL Tape

Revision History

BSC010N04LS

Revision: 2014-06-27, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.2	2014-06-27	Rev. 2.2

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